

DDTC (R2-ONLY SERIES) E

NPN PRE-BIASED SMALL SIGNAL SOT-523 SURFACE MOUNT TRANSISTOR

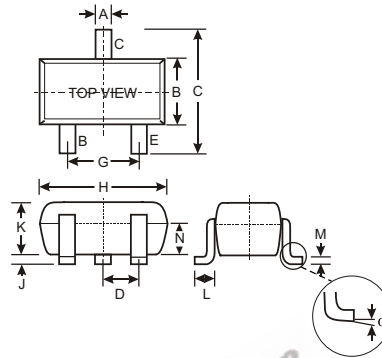
NEW PRODUCT

Features

- Epitaxial Planar Die Construction
- Complementary PNP Types Available (DDTA)
- Built-In Biasing Resistor, R2 only

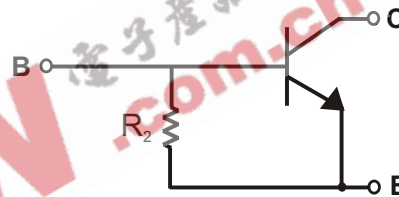
Mechanical Data

- Case: SOT-523, Molded Plastic
- Case material - UL Flammability Rating 94V-0
- Moisture sensitivity: Level 1 per J-STD-020A
- Terminals: Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking: Date Code and Marking Code (See Diagrams & Page 2)
- Weight: 0.002 grams (approx.)
- Ordering Information (See Page 2)



SOT-523			
Dim	Min	Max	Typ
A	0.15	0.30	0.22
B	0.75	0.85	0.80
C	1.45	1.75	1.60
D	—	—	0.50
G	0.90	1.10	1.00
H	1.50	1.70	1.60
J	0.00	0.10	0.05
K	0.60	0.80	0.75
L	0.10	0.30	0.22
M	0.10	0.20	0.12
N	0.45	0.65	0.50
α	0°	8°	—
All Dimensions in mm			

P/N	R2 (NOM)	MARKING
DDTC114GE	10K Ω	N26
DDTC124GE	22K Ω	N27
DDTC144GE	47K Ω	N28
DDTC115GE	100K Ω	N29



SCHMATIC DIAGRAM

Maximum Ratings @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	50	V
Collector-Emitter Voltage	V _{CEO}	50	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current	I _C (Max)	100	mA
Power Dissipation	P _d	150	mW
Thermal Resistance, Junction to Ambient Air (Note 1)	R _{θJA}	833	°C/W
Operating and Storage and Temperature Range	T _J , T _{STG}	-55 to +150	°C

Note: 1. Mounted on FR4 PC Board with recommended pad layout, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.

Electrical Characteristics @ T_A = 25°C unless otherwise specified

Characteristic		Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage		BV _{CBO}	50	—	—	V	I _C = 50μA
Collector-Emitter Breakdown Voltage		BV _{CEO}	50	—	—	V	I _C = 1mA
Emitter-Base Breakdown Voltage		BV _{EBO}	5	—	—	V	I _E = 720μA, DDTC114GE I _E = 330μA, DDTC124GE I _E = 160μA, DDTC144GE I _E = 72μA, DDTC115GE
Collector Cutoff Current		I _{CBO}	—	—	0.5	μA	V _{CB} = 50V
Emitter Cutoff Current	DDTC114GE	I _{EBO}	300	—	580	μA	V _{EB} = 4V
	DDTC124GE		140		260		
	DDTC144GE		65		130		
	DDTC115GE		30		58		
Collector-Emitter Saturation Voltage		V _{CE(sat)}	—	—	0.3	V	I _C = 10mA, I _B = 0.5mA
DC Current Transfer Ratio	DDTC114GE	h _{FE}	30	—	—	—	I _C = 5mA, V _{CE} = 5V
	DDTC124GE		56				
	DDTC144GE		68				
	DDTC115GE		82				
Bleeder Resistor (R ₂) Tolerance		DR ₂	-30	—	+30	%	—
Gain-Bandwidth Product*		f _T	—	250	—	MHz	V _{CE} = 10V, I _E = -5mA, f = 100MHz

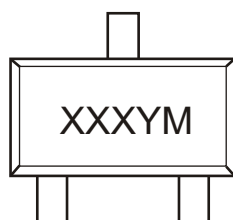
* Transistor - For Reference Only

Ordering Information (Note 2)

Device	Packaging	Shipping
DDTC114GE-7	SOT-523	3000/Tape & Reel
DDTC124GE-7	SOT-523	3000/Tape & Reel
DDTC144GE-7	SOT-523	3000/Tape & Reel
DDTC115GE-7	SOT-523	3000/Tape & Reel

Notes: 2. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



XXX = Product Type Marking Code (See Page 1, e.g. N26 = DDTC114GE)
 YM = Date Code Marking
 Y = Year (ex: N = 2002)
 M = Month (ex: 9 = September)

Date Code Key

Year	2002	2003	2004	2005	2006	2007	2008	2009
Code	N	P	R	S	T	U	V	W

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

TYPICAL CURVES - DDTC114GE

